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## Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

## Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

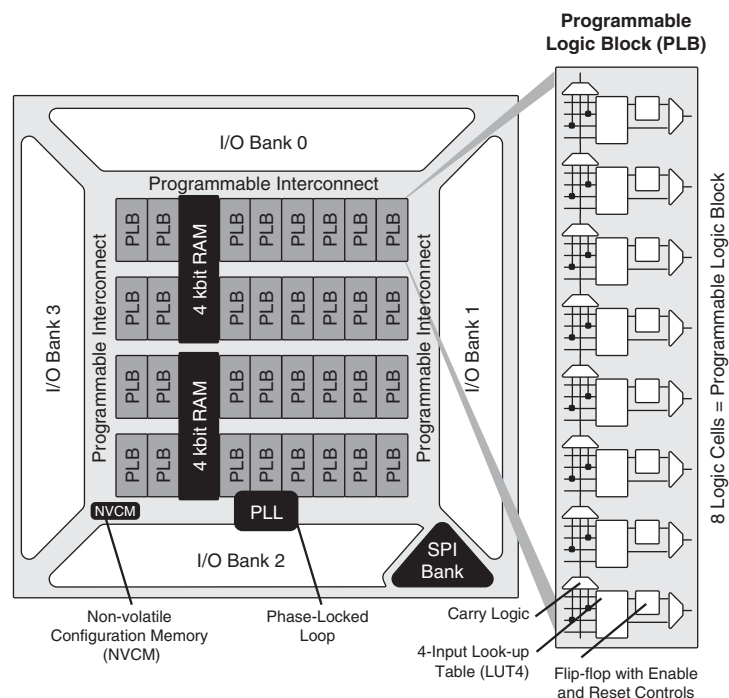
### Details

Product Status	Active
Number of LABs/CLBs	48
Number of Logic Elements/Cells	384
Total RAM Bits	-
Number of I/O	37
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	49-VFBGA
Supplier Device Package	49-UCBGA (3x3)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/lattice-semiconductor/ice40lp384-cm49tr1k">https://www.e-xfl.com/product-detail/lattice-semiconductor/ice40lp384-cm49tr1k</a>

## Architecture Overview

The iCE40 family architecture contains an array of Programmable Logic Blocks (PLB), sysCLOCK™ PLLs, Non-volatile Programmable Configuration Memory (NVCM) and blocks of sysMEM™ Embedded Block RAM (EBR) surrounded by Programmable I/O (PIO). Figure 2-1 shows the block diagram of the iCE40LP/HX1K device.

**Figure 2-1. iCE40LP/HX1K Device, Top View**



The logic blocks, Programmable Logic Blocks (PLB) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each column has either logic blocks or EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PLB contains the building blocks for logic, arithmetic, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the iCE40 family, there are up to four independent sysIO banks. Note on some packages  $V_{CCIO}$  banks are tied together. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large 4 kbit, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO.

The iCE40 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

Every device in the family has a SPI port that supports programming and configuration of the device. The iCE40 includes on-chip, Nonvolatile Configuration Memory (NVCM).

## Global Reset Control

The global reset control signal connects to all PLB and PIO flip-flops on the iCE40 device. The global reset signal is automatically asserted throughout the configuration process, forcing all flip-flops to their defined wake-up state. For PLB flip-flops, the wake-up state is always reset, regardless of the PLB flip-flop primitive used in the application.

## sysCLOCK Phase Locked Loops (PLLs)

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The iCE40 devices have one or more sysCLOCK PLLs. REFERENCECLK is the reference frequency input to the PLL and its source can come from an external I/O pin or from internal routing. EXTFEEDBACK is the feedback signal to the PLL which can come from internal routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The PLLOUT output has an output divider, thus allowing the PLL to generate different frequencies for each output. The output divider can have a value from 1 to 6. The PLLOUT outputs can all be used to drive the iCE40 global clock network directly or general purpose routing resources can be used.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected. A block diagram of the PLL is shown in Figure 2-3.

The timing of the device registers can be optimized by programming a phase shift into the PLLOUT output clock which will advance or delay the output clock with reference to the REFERENCECLK clock. This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the  $t_{LOCK}$  parameter has been satisfied.

For more details on the PLL, see TN1251, [iCE40 sysCLOCK PLL Design and Usage Guide](#).

**Figure 2-3. PLL Diagram**

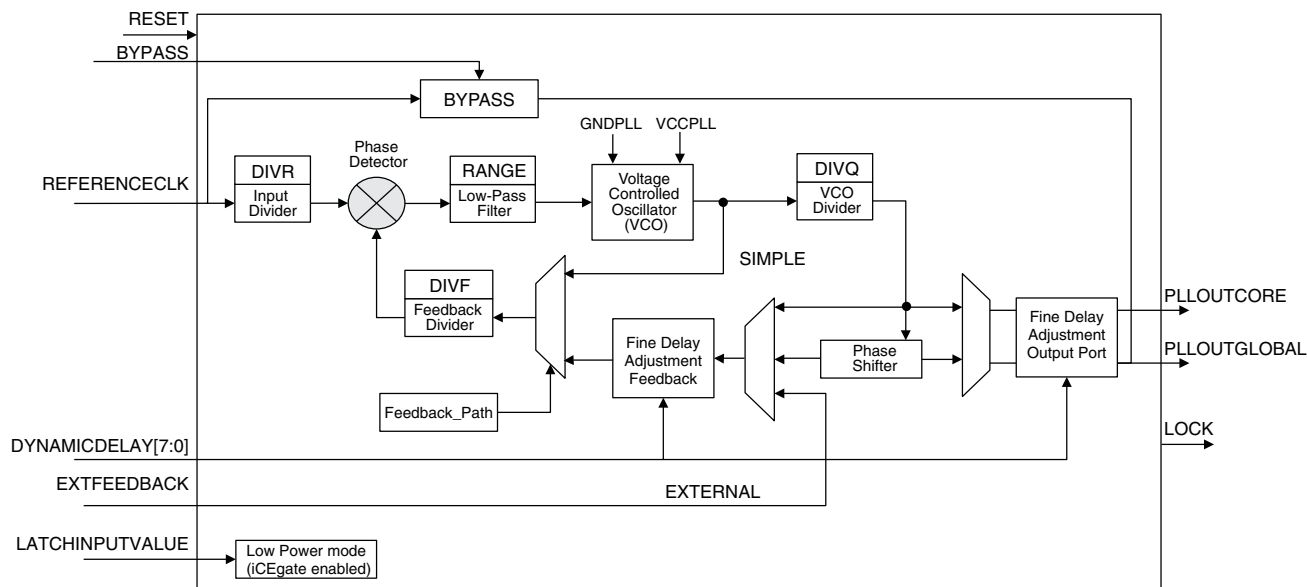


Table 2-3 provides signal descriptions of the PLL block.

fers. Bank 3 additionally supports differential LVDS25 input buffers. Each sysIO bank has its own dedicated power supply.

### Typical I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when  $V_{CC}$ ,  $V_{CCIO\_2}$ ,  $V_{PP\_2V5}$ , and  $V_{CC\_SPI}$  have reached the level defined in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all  $V_{CCIO}$  banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. The default configuration of the I/O pins in a device prior to configuration is tri-stated with a weak pull-up to  $V_{CCIO}$ . The I/O pins will maintain the pre-configuration state until  $V_{CC}$  and  $V_{CCIO}$  (for I/O banks containing configuration I/Os) have reached levels, at which time the I/Os will take on the software user-configured settings only after a proper download/configuration. Unused I/Os are automatically blocked and the pullup termination is disabled.

### Supported Standards

The iCE40 sysIO buffer supports both single-ended and differential input standards. The single-ended standard supported is LVC MOS. The buffer supports the LVC MOS 1.8, 2.5, and 3.3 V standards. The buffer has individually configurable options for bus maintenance (weak pull-up or none). The High Current output buffer have individually configurable options for drive strength.

Table 2-7 and Table 2-8 show the I/O standards (together with their supply and reference voltages) supported by the iCE40 devices.

**Table 2-7. Supported Input Standards**

Input Standard	$V_{CCIO}$ (Typical)		
	3.3 V	2.5 V	1.8 V
<b>Single-Ended Interfaces</b>			
LVC MOS33	Yes		
LVC MOS25		Yes	
LVC MOS18			Yes
<b>Differential Interfaces</b>			
LVDS25 <sup>1</sup>		Yes	
subLVDS <sup>1</sup>			Yes

1. Bank 3 only.

**Table 2-8. Supported Output Standards**

Output Standard	$V_{CCIO}$ (Typical)
<b>Single-Ended Interfaces</b>	
LVC MOS33	3.3
LVC MOS25	2.5
LVC MOS18	1.8
<b>Differential Interfaces</b>	
LVDS25E <sup>1</sup>	2.5
subLVDSE <sup>1</sup>	1.8

1. These interfaces can be emulated with external resistors in all devices.

### Non-Volatile Configuration Memory

All iCE40 devices provide a Non-Volatile Configuration Memory (NVCM) block which can be used to configure the device.

For more information on the NVCM, please refer to TN1248, [iCE40 Programming and Configuration Usage Guide](#).

### DC Electrical Characteristics

#### Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$I_{IL}, I_{IH}^{1, 3, 4, 5, 6, 7}$	Input or I/O Leakage	$0V < V_{IN} < V_{CCIO} + 0.2V$	—	—	+/-10	$\mu A$
$C_1^{6, 7}$	I/O Capacitance <sup>2</sup>	$V_{CCIO} = 3.3V, 2.5V, 1.8V$ $V_{CC} = \text{Typ.}, V_{IO} = 0 \text{ to } V_{CCIO} + 0.2V$	—	6	—	pf
$C_2^{6, 7}$	Global Input Buffer Capacitance <sup>2</sup>	$V_{CCIO} = 3.3V, 2.5V, 1.8V$ $V_{CC} = \text{Typ.}, V_{IO} = 0 \text{ to } V_{CCIO} + 0.2V$	—	6	—	pf
$V_{HYST}$	Input Hysteresis	$V_{CCIO} = 1.8V, 2.5V, 3.3V$	—	200	—	mV
$I_{PU}^{6, 7}$	Internal PIO Pull-up Current	$V_{CCIO} = 1.8V, 0 \leq V_{IN} \leq 0.65 V_{CCIO}$	-3	—	-31	$\mu A$
		$V_{CCIO} = 2.5V, 0 \leq V_{IN} \leq 0.65 V_{CCIO}$	-8	—	-72	$\mu A$
		$V_{CCIO} = 3.3V, 0 \leq V_{IN} \leq 0.65 V_{CCIO}$	-11	—	-128	$\mu A$

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Internal pull-up resistors are disabled.
2.  $T_J = 25^\circ C$ ,  $f = 1.0 \text{ MHz}$ .
3. Please refer to  $V_{IL}$  and  $V_{IH}$  in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. Only applies to IOs in the SPI bank following configuration.
5. Some products are clamped to a diode when  $V_{IN}$  is larger than  $V_{CCIO}$ .
6. High current IOs has three sysIO buffers connected together.
7. The iCE40LP640 and iCE40LP1K SWG16 package has CDONE and a sysIO buffer are connected together.

### Static Supply Current – LP Devices<sup>1, 2, 3, 4</sup>

Symbol	Parameter	Device	Typ. $V_{CC}^4$	Units
$I_{CC}$	Core Power Supply	iCE40LP384	21	$\mu A$
		iCE40LP640	100	$\mu A$
		iCE40LP1K	100	$\mu A$
		iCE40LP4K	250	$\mu A$
		iCE40LP8K	250	$\mu A$
$I_{CCPLL}^{5, 6}$	PLL Power Supply	All devices	0.5	$\mu A$
$I_{PP\_2V5}$	NVCM Power Supply	All devices	1.0	$\mu A$
$I_{CCIO}, I_{CC\_SPI}$	Bank Power Supply <sup>4</sup> $V_{CCIO} = 2.5V$	All devices	3.5	$\mu A$

1. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at  $V_{CCIO}$  or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.
2. Frequency = 0 MHz.
3.  $T_J = 25^\circ C$ , power supplies at nominal voltage.
4. Does not include pull-up.
5. No PLL available on the iCE40LP384 and iCE40LP640 device.
6.  $V_{CCPLL}$  is tied to  $V_{CC}$  internally in packages without PLLs pins.

### Programming NVCM Supply Current – HX Devices<sup>1, 2, 3, 4</sup>

Symbol	Parameter	Device	Typ. $V_{CC}^5$	Units
$I_{CC}$	Core Power Supply	iCE40HX1K	278	$\mu A$
		iCE40HX4K	1174	$\mu A$
		iCE40HX8K	1174	$\mu A$
$I_{CCPLL}^6$	PLL Power Supply	All devices	0.5	$\mu A$
$I_{PP\_2V5}$	NVCM Power Supply	All devices	2.5	mA
$I_{CCIO}^7, I_{CC\_SPI}$	Bank Power Supply <sup>5</sup>	All devices	3.5	mA

1. Assumes all inputs are held at  $V_{CCIO}$  or GND and all outputs are tri-stated.

2. Typical user pattern.

3. SPI programming is at 8 MHz.

4.  $T_J = 25^\circ C$ , power supplies at nominal voltage.

5. Per bank.  $V_{CCIO} = 2.5 V$ . Does not include pull-up.

6.  $V_{CCPLL}$  is tied to  $V_{CC}$  internally in packages without PLLs pins.

7.  $V_{PP\_FAST}$ , used only for fast production programming, must be left floating or unconnected in applications.

### Peak Startup Supply Current – LP Devices

Symbol	Parameter	Device	Max	Units
$I_{CCPEAK}$	Core Power Supply	iCE40LP384	7.7	mA
		iCELP640	6.4	mA
		iCE40LP1K	6.4	mA
		iCE40LP4K	15.7	mA
		iCE40LP8K	15.7	mA
$I_{CCPLLPEAK}^{1, 2, 4}$	PLL Power Supply	iCE40LP1K	1.5	mA
		iCELP640	1.5	mA
		iCE40LP4K	8.0	mA
		iCE40LP8K	8.0	mA
$I_{PP\_2V5PEAK}$	NVCM Power Supply	iCE40LP384	3.0	mA
		iCELP640	7.7	mA
		iCE40LP1K	7.7	mA
		iCE40LP4K	4.2	mA
		iCE40LP8K	4.2	mA
$I_{PP\_FASTPEAK}^3$	NVCM Programming Supply	iCE40LP384	5.7	mA
		iCELP640	8.1	mA
		iCE40LP1K	8.1	mA
$I_{CCIOPEAK}^5, I_{CC\_SPIPEAK}$	Bank Power Supply	iCE40LP384	8.4	mA
		iCELP640	3.3	mA
		iCE40LP1K	3.3	mA
		iCE40LP4K	8.2	mA
		iCE40LP8K	8.2	mA

1. No PLL available on the iCE40LP384 and iCE40LP640 device.

2.  $V_{CCPLL}$  is tied to  $V_{CC}$  internally in packages without PLLs pins.

3.  $V_{PP\_FAST}$ , used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the  $V_{PP\_FAST}$  ball connected to  $V_{CCIO\_0}$  ball externally.

4. While no PLL is available in the iCE40-LP640 the  $I_{CCPLLPEAK}$  is additive to  $I_{CCPEAK}$ .

5. iCE40LP384 requires  $V_{CC}$  to be greater than 0.7 V when  $V_{CCIO}$  and  $V_{CC\_SPI}$  are above GND.

### Peak Startup Supply Current – HX Devices

Symbol	Parameter	Device	Max	Units
$I_{CCPEAK}$	Core Power Supply	iCE40HX1K	6.9	mA
		iCE40HX4K	22.3	mA
		iCE40HX8K	22.3	mA
$I_{CCPLLPEAK}^1$	PLL Power Supply	iCE40HX1K	1.8	mA
		iCE40HX4K	6.4	mA
		iCE40HX8K	6.4	mA
$I_{PP\_2V5PEAK}$	NVCM Power Supply	iCE40HX1K	2.8	mA
		iCE40HX4K	4.1	mA
		iCE40HX8K	4.1	mA
$I_{CCIOPEAK}, I_{CC\_SPIPEAK}$	Bank Power Supply	iCE40HX1K	6.8	mA
		iCE40HX4K	6.8	mA
		iCE40HX8K	6.8	mA

1.  $V_{CCPLL}$  is tied to  $V_{CC}$  internally in packages without PLLs pins.

### sysIO Recommended Operating Conditions

Standard	$V_{CCIO}$ (V)		
	Min.	Typ.	Max.
LVC MOS 3.3	3.14	3.3	3.46
LVC MOS 2.5	2.37	2.5	2.62
LVC MOS 1.8	1.71	1.8	1.89
LVDS25E <sup>1,2</sup>	2.37	2.5	2.62
subLVDSE <sup>1,2</sup>	1.71	1.8	1.89

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.

2. Does not apply to Configuration Bank  $V_{CC\_SPI}$ .

### sysIO Single-Ended DC Electrical Characteristics

Input/ Output Standard	$V_{IL}$		$V_{IH}^1$		$V_{OL}$ Max. (V)	$V_{OH}$ Min. (V)	$I_{OL}$ Max. (mA)	$I_{OH}$ Max. (mA)
	Min. (V)	Max. (V)	Min. (V)	Max. (V)				
LVC MOS 3.3	-0.3	0.8	2.0	$V_{CCIO} + 0.2$ V	0.4	$V_{CCIO} - 0.4$	8, 16 <sup>2</sup> , 24 <sup>2</sup>	-8, -16 <sup>2</sup> , -24 <sup>2</sup>
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVC MOS 2.5	-0.3	0.7	1.7	$V_{CCIO} + 0.2$ V	0.4	$V_{CCIO} - 0.4$	6, 12 <sup>2</sup> , 18 <sup>2</sup>	-6, -12 <sup>2</sup> , -18 <sup>2</sup>
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVC MOS 1.8	-0.3	0.35 $V_{CCIO}$	0.65 $V_{CCIO}$	$V_{CCIO} + 0.2$ V	0.4	$V_{CCIO} - 0.4$	4, 8 <sup>2</sup> , 12 <sup>2</sup>	-4, -8 <sup>2</sup> , -12 <sup>2</sup>
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1

1. Some products are clamped to a diode when  $V_{IN}$  is larger than  $V_{CCIO}$ .

2. Only for High Drive LED outputs.

## sysIO Differential Electrical Characteristics

The LVDS25E/subLVDS differential output buffers are available on all banks but the LVDS/subLVDS input buffers are only available on Bank 3 of iCE40 devices.

### LVDS25

#### Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
$V_{INP}, V_{INM}$	Input Voltage	$V_{CCIO}^1 = 2.5$	0	—	2.5	V
$V_{THD}$	Differential Input Threshold		250	350	450	mV
$V_{CM}$	Input Common Mode Voltage	$V_{CCIO}^1 = 2.5$	$(V_{CCIO}/2) - 0.3$	$V_{CCIO}/2$	$(V_{CCIO}/2) + 0.3$	V
$I_{IN}$	Input Current	Power on	—	—	$\pm 10$	$\mu A$

1. Typical.

### subLVDS

#### Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
$V_{INP}, V_{INM}$	Input Voltage	$V_{CCIO}^1 = 1.8$	0	—	1.8	V
$V_{THD}$	Differential Input Threshold		100	150	200	mV
$V_{CM}$	Input Common Mode Voltage	$V_{CCIO}^1 = 1.8$	$(V_{CCIO}/2) - 0.25$	$V_{CCIO}/2$	$(V_{CCIO}/2) + 0.25$	V
$I_{IN}$	Input Current	Power on	—	—	$\pm 10$	$\mu A$

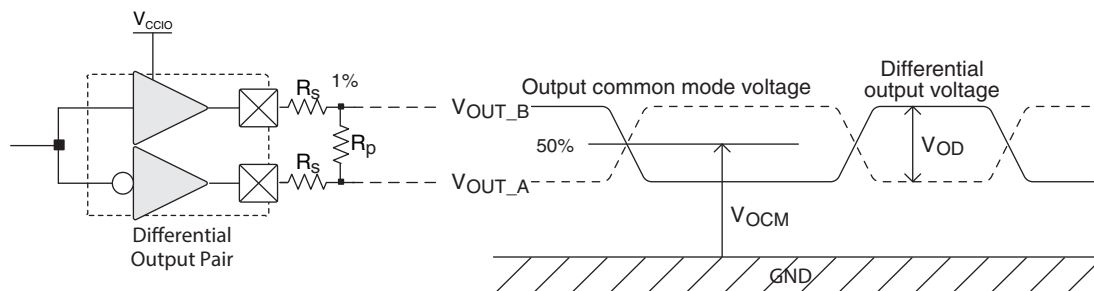
1. Typical.



### LVDS25E Emulation

iCE40 devices can support LVDS25E outputs via emulation on all banks. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS25E standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

**Figure 3-1. LVDS25E Using External Resistors**



**Table 3-1. LVDS25E DC Conditions**

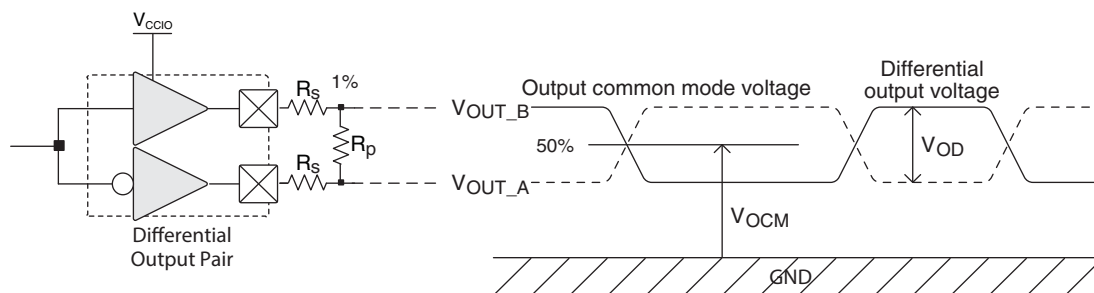
#### Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
$Z_{OUT}$	Output impedance	20	Ohms
$R_S$	Driver series resistor	150	Ohms
$R_P$	Driver parallel resistor	140	Ohms
$R_T$	Receiver termination	100	Ohms
$V_{OH}$	Output high voltage	1.43	V
$V_{OL}$	Output low voltage	1.07	V
$V_{OD}$	Output differential voltage	0.30	V
$V_{CM}$	Output common mode voltage	1.25	V
$Z_{BACK}$	Back impedance	100.5	Ohms
$I_{DC}$	DC output current	6.03	mA

### SubLVDS Emulation

The iCE40 family supports the differential subLVDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all banks of the devices. The subLVDS input standard is supported by the LVDS25 differential input buffer. The scheme shown in Figure 3-2 is one possible solution for subLVDS output standard implementation. Use LVDS25E mode with suggested resistors for subLVDS operation. Resistor values in Figure 3-2 are industry standard values for 1% resistors.

**Figure 3-2. subLVDS**



**Table 3-2. subLVDS DC Conditions**

#### Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
$Z_{OUT}$	Output impedance	20	Ohms
$R_S$	Driver series resistor	270	Ohms
$R_P$	Driver parallel resistor	120	Ohms
$R_T$	Receiver termination	100	Ohms
$V_{OH}$	Output high voltage	1.43	V
$V_{OL}$	Output low voltage	1.07	V
$V_{OD}$	Output differential voltage	0.35	V
$V_{CM}$	Output common mode voltage	0.9	V
$Z_{BACK}$	Back impedance	100.5	Ohms
$I_{DC}$	DC output current	2.8	mA

## Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

## Maximum sysIO Buffer Performance<sup>2</sup>

I/O Standard	Max. Speed	Units
<b>Inputs</b>		
LVDS25 <sup>1</sup>	400	MHz
subLVDS18 <sup>1</sup>	400	MHz
LVC MOS33	250	MHz
LVC MOS25	250	MHz
LVC MOS18	250	MHz
<b>Outputs</b>		
LVDS25E	250	MHz
subLVDS18E	155	MHz
LVC MOS33	250	MHz
LVC MOS25	250	MHz
LVC MOS18	155	MHz

1. Supported in Bank 3 only.

2. Measured with a toggling pattern

## iCE40 Family Timing Adders

Over Recommended Commercial Operating Conditions - LP Devices<sup>1, 2, 3, 4, 5</sup>

Buffer Type	Description	Timing	Units
<b>Input Adjusters</b>			
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	-0.18	ns
subLVDS	subLVDS, $V_{CCIO} = 1.8\text{ V}$	0.82	ns
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	0.18	ns
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	0.19	ns
<b>Output Adjusters</b>			
LVDS25E	LVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
subLVDS25E	subLVDS, Emulated, $V_{CCIO} = 1.8\text{ V}$	1.32	ns
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	-0.12	ns
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	1.32	ns

1. Timing adders are relative to LVC MOS25 and characterized but not tested on every device.

2. LVC MOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Commercial timing numbers are shown.

5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.

**Over Recommended Commercial Operating Conditions - HX Devices<sup>1, 2, 3, 4, 5</sup>**

Buffer Type	Description	Timing	Units
<b>Input Adjusters</b>			
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	0.13	ns
subLVDS	subLVDS, $V_{CCIO} = 1.8\text{ V}$	1.03	ns
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	0.16	ns
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	0.23	ns
<b>Output Adjusters</b>			
LVDS25E	LVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
subLVDS E	subLVDS, Emulated, $V_{CCIO} = 1.8\text{ V}$	1.76	ns
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	0.17	ns
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	1.76	ns

1. Timing adders are relative to LVC MOS25 and characterized but not tested on every device.
2. LVC MOS timing measured with the load specified in Switching Test Condition table.
3. All other standards tested according to the appropriate specifications.
4. Commercial timing numbers are shown.
5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.

**iCE40 External Switching Characteristics – LP Devices (Continued)<sup>1, 2</sup>**
**Over Recommended Operating Conditions**

Parameter	Description	Device	Min.	Max.	Units
t <sub>HPLL</sub>	Clock to Data Hold - PIO Input Register	iCE40LP1K	–0.90	—	ns
		iCE40LP4K	–0.80	—	ns
		iCE40LP8K	–0.80	—	ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions can be extracted from the iCECube2 software.

2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.

3. Supported on devices with a PLL.

**SPI Master or NVCM Configuration Time<sup>1, 2</sup>**

Symbol	Parameter	Conditions	Typ.	Units
$t_{\text{CONFIG}}$	POR/CRESET_B to Device I/O Active	iCE40LP384 - Low Frequency (Default)	25	ms
		iCE40LP384 - Medium Frequency	15	ms
		iCE40LP384 - High Frequency	11	ms
		iCE40LP640 - Low Frequency (Default)	53	ms
		iCE40LP640 - Medium Frequency	25	ms
		iCE40LP640 - High Frequency	13	ms
		iCE40LP/HX1K - Low Frequency (Default)	53	ms
		iCE40LP/HX1K - Medium Frequency	25	ms
		iCE40LP/HX1K - High Frequency	13	ms
		iCE40LP/HX4K - Low Frequency (Default)	230	ms
		iCE40LP/HX4K - Medium Frequency	110	ms
		iCE40LP/HX4K - High Frequency	70	ms
		iCE40LP/HX8K - Low Frequency (Default)	230	ms
		iCE40LP/HX8K - Medium Frequency	110	ms
		iCE40LP/HX8K - High Frequency	70	ms

1. Assumes sysMEM Block is initialized to an all zero pattern if they are used.

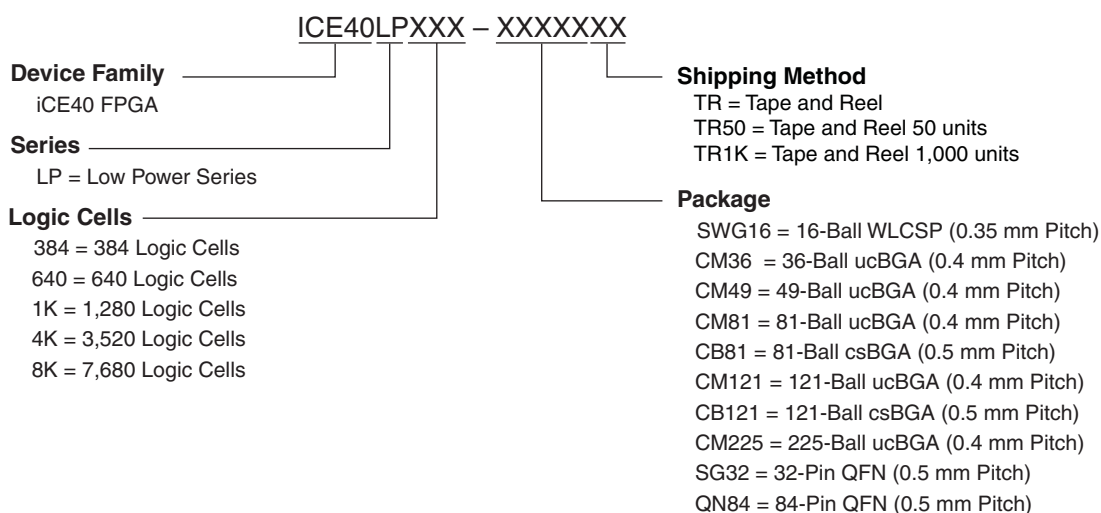
2. The NVCM download time is measured with a fast ramp rate starting from the maximum voltage of POR trip point.

**sysCONFIG Port Timing Specifications<sup>1</sup>**

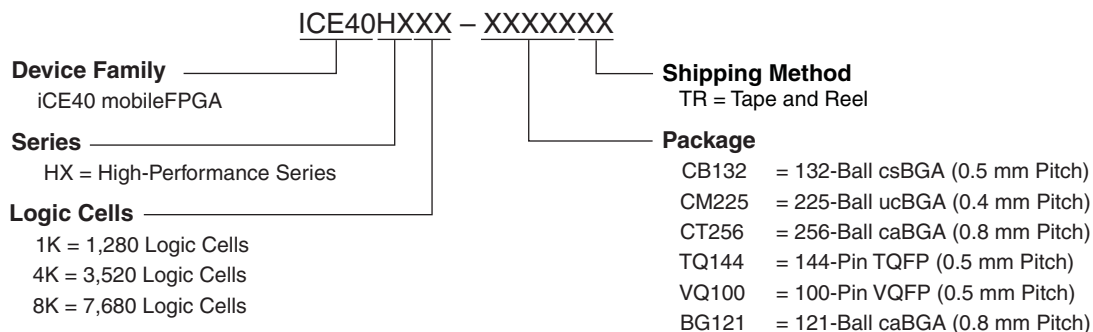
Symbol	Parameter		Min.	Typ.	Max.	Units
<b>All Configuration Modes</b>						
$t_{\text{CRESET\_B}}$	Minimum CRESET_B Low pulse width required to restart configuration, from falling edge to rising edge		200	—	—	ns
$t_{\text{DONE\_IO}}$	Number of configuration clock cycles after CDONE goes High before the PIO pins are activated		49	—	—	Clock Cycles
<b>Slave SPI</b>						
$t_{\text{CR\_SCK}}$	Minimum time from a rising edge on CRESET_B until the first SPI write operation, first SPI_SCK. During this time, the iCE40 device is clearing its internal configuration memory	iCE40LP384	600	-	—	us
		iCE40LP640, iCE40LP/HX1K	800	-	—	us
		iCE40LP/HX4K	1200	-	—	us
		iCE40LP/HX8K	1200	-	—	us
$f_{\text{MAX}}^1$	CCLK clock frequency	Write	1	-	25	MHz
		Read iCE40LP384 <sup>2</sup>	-	15	-	MHz
		Read iCE40LP640, iCE40LP/HX1K <sup>2</sup>	-	15	-	MHz
		Read iCE40LP/HX4K <sup>2</sup>	-	15	-	MHz
		Read iCE40LP/HX8K <sup>2</sup>	-	15	-	MHz
$t_{\text{CCLKH}}$	CCLK clock pulse width high		20	—	—	ns
$t_{\text{CCLKL}}$	CCLK clock pulse width low		20	—	—	ns
$t_{\text{STSU}}$	CCLK setup time		12	—	—	ns
$t_{\text{STH}}$	CCLK hold time		12	—	—	ns
$t_{\text{STCO}}$	CCLK falling edge to valid output		13	—	—	ns
<b>Master SPI</b>						
$f_{\text{MCLK}}$	MCLK clock frequency	Off	—	0	—	MHz
		Low Frequency (Default)	—	7.5	—	MHz
		Medium Frequency <sup>3</sup>	—	24	—	MHz
		High Frequency <sup>3</sup>	—	40	—	MHz

### iCE40 Part Number Description

#### Ultra Low Power (LP) Devices



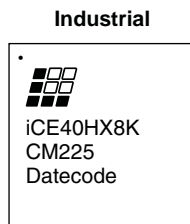
#### High Performance (HX) Devices



All parts shipped in trays unless noted.

### Ordering Information

iCE40 devices have top-side markings as shown below:



Note: Markings are abbreviated for small packages.



Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40LP8K-CM121TR1K	7680	1.2 V	Halogen-Free ucBGA	121	IND
ICE40LP8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND

### High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Package	Leads	Temp.
ICE40HX1K-CB132	1280	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX1K-VQ100	1280	1.2 V	Halogen-Free VQFP	100	IND
ICE40HX1K-TQ144	1280	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX4K-BG121	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-BG121TR	3520	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX4K-CB132	3520	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX4K-TQ144	3520	1.2 V	Halogen-Free TQFP	144	IND
ICE40HX8K-BG121	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-BG121TR	7680	1.2 V	Halogen-Free caBGA	121	IND
ICE40HX8K-CB132	7680	1.2 V	Halogen-Free csBGA	132	IND
ICE40HX8K-CM225	7680	1.2 V	Halogen-Free ucBGA	225	IND
ICE40HX8K-CT256	7680	1.2 V	Halogen-Free caBGA	256	IND

## For Further Information

A variety of technical notes for the iCE40 family are available on the Lattice web site.

- [TN1248, iCE40 Programming and Configuration](#)
- [TN1250, Memory Usage Guide for iCE40 Devices](#)
- [TN1251, iCE40 sysCLOCK PLL Design and Usage Guide](#)
- [TN1252, iCE40 Hardware Checklist](#)
- [TN1253, Using Differential I/O \(LVDS, Sub-LVDS\) in iCE40 Devices](#)
- [TN1074, PCB Layout Recommendations for BGA Packages](#)
- [iCE40 Pinout Files](#)
- [Thermal Management](#) document
- [Lattice design tools](#)
- [IBIS](#)
- [Package Diagrams Data Sheet](#)
- [Schematic Symbols](#)

# iCE40 LP/HX Family Data Sheet

## Revision History

March 2017

Data Sheet DS1040

Date	Version	Section	Change Summary
March 2017	3.3	Introduction	Updated <a href="#">Features</a> section. Added 121-ball caBGA package for ICE40 HX4K/8K to Table 1-1, iCE40 Family Selection Guide.
		Architecture	Updated <a href="#">PLB Blocks</a> section. Changed “subtractors” to “subtractions” in the Carry Logic description.
			Updated <a href="#">Clock/Control Distribution Network</a> section. Switched the “Clock Enable” and the “Reset” headings in Table 2-2, Global Buffer (GBUF) Connections to Programmable Logic Blocks.
		Pinout Information	Updated <a href="#">Pin Information Summary</a> section. Added BG121 information under iCE40HX4K and iCE40HX8K.
		Ordering Information	Updated <a href="#">iCE40 Part Number Description</a> section. Added Shipping Method and BG121 package under High Performance (HX) Devices.
			Updated <a href="#">Ordering Information</a> section. Added part numbers for BG121 under High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging.
		Supplemental Information	Corrected reference to “Package Diagrams Data Sheet”.
October 2015	3.2	Introduction	Updated Features section. Added footnote to 16 WLCSP Programmable I/O: Max Inputs (LVDS25) in Table 1-1, iCE40 Family Selection Guide.
		DC and Switching Characteristics	Updated sysCLOCK PLL Timing section. Changed $t_{DT}$ conditions. Updated Programming NVCM Supply Current – LP Devices section. Changed $I_{PP\_2V5}$ and $I_{CCIO}$ , $I_{CC\_SPI}$ units.
March 2015	3.1	DC and Switching Characteristics	Updated sysIO Single-Ended DC Electrical Characteristics section. Changed LVCMOS 3.3 and LVCMOS 2.5 $V_{OH}$ Min. (V) from 0.5 to 0.4.
July 2014	3.0	DC and Switching Characteristics	Revised and/or added Typ. $V_{CC}$ data in the following sections. — Static Supply Current – LP Devices — Static Supply Current – HX Devices — Programming NVCM Supply Current – LP Devices — Programming NVCM Supply Current – HX Devices In each section table, the footnote indicating Advanced device status was removed.
		Pinout Information	Updated Pin Information Summary section. Added footnote 1 to CM49 under iCE40LP1K.
April 2014	02.9	Ordering Information	Changed “i” to “I” in part number description and ordering part numbers.
			Added part numbers to the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.

Date	Version	Section	Change Summary
February 2014	02.8	Introduction	Updated Features section. — Corrected standby power units. — Included High Current LED Drivers
			Updated Table 1-1, iCE40 Family Selection Guide. — Removed LP384 Programmable I/O for 81 ucBGA package.
		Architecture	Updated Supported Standards section. Added information on High Current LED drivers.
		DC and Switching Characteristics	Corrected typos.
			Added footnote to the Peak Startup Supply Current – LP Devices table.
		Ordering Information	Updated part number description in the Ultra Low Power (LP) Devices section.
			Added part numbers to the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.
October 2013	02.7	Introduction	Updated Features list and iCE40 Family Selection Guide table.
		Architecture	Revised iCE40-1K device to iCE40LP/HX1K device.
		DC and Switching Characteristics	Added iCE40LP640 device information.
		Pinout Information	Added iCE40LP640 and iCE40LP1K information.
		Ordering Information	Added iCE40LP640 and iCE40LP1K information.
September 2013	02.6	DC and Switching Characteristics	Updated Absolute Maximum Ratings section.
			Updated sysCLOCK PLL Timing – Preliminary table.
		Pinout Information	Updated Pin Information Summary table.
August 2013	02.5	Introduction	Updated the iCE40 Family Selection Guide table.
		DC and Switching Characteristics	Updated the following tables: — Absolute Maximum Ratings — Power-On-Reset Voltage Levels — Static Supply Current – LP Devices — Static Supply Current – HX Devices — Programming NVCM Supply Current – LP Devices — Programming NVCM Supply Current – HX Devices — Peak Startup Supply Current – LP Devices — sysIO Recommended Operating Conditions — Typical Building Block Function Performance – HX Devices — iCE40 External Switching Characteristics – HX Devices — sysCLOCK PLL Timing – Preliminary — SPI Master or NVCM Configuration Time
		Pinout Information	Updated the Pin Information Summary table.
July 2013	02.4	Introduction	Updated the iCE40 Family Selection Guide table.
		DC and Switching Characteristics	Updated the sysCONFIG Port Timing Specifications table.
			Updated footnote in DC Electrical Characteristics table.
			GDDR tables removed. Support to be provided in a technical note.
		Pinout Information	Updated the Pin Information Summary table.
		Ordering Information	Updated the top-side markings figure.
			Updated the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.
May 2013	02.3	DC and Switching Characteristics	Added new data from Characterization.

Date	Version	Section	Change Summary
April 2013	02.2	Introduction	Added the LP8K 81 ucBGA.
		Architecture	Corrected typos.
		DC and Switching Characteristics	Corrected typos. Added 7:1 LVDS waveforms.
		Pinout Information	Corrected typos in signal descriptions. Added the LP8K 81 ucBGA.
		Ordering Information	Added the LP8K 81 ucBGA.
March 2013	02.1	DC and Switching Characteristics	Recommended operating conditions added requirement for Master SPI.
			Updated Recommended Operating Conditions for $V_{PP\_2V5}$ .
			Updated Power-On-Reset Voltage Levels and sequence requirements.
			Updated Static Supply Current conditions.
			Changed unit for $t_{SKEW\_IO}$ from ns to ps.
			Updated range of CCLK $f_{MAX}$ .
		Ordering Information	Updated ordering information to include tape and reel part numbers.
September 2012	02.0	—	Merged SiliconBlue iCE40 LP and HX data sheets and updated to Lattice format.
	01.31	—	Updated Table 1.
	01.3	—	Production release.
			Updated notes on Table 3: Recommended Operating Conditions.
			Updated values in Table 4, Table 5, Table 12, Table 13 and Table 17.
	01.21	—	Updated Figure 3 and Figure 4 to specify iCE40.
Aug 2012	01.2	—	Updated company name.
July 2011	01.1	—	Moved package specifications to iCE40 pinout Excel files.
			Updated Table 1 maximum I/Os.
	01.01	—	Added 640, 1K and 4K to Table 13 configuration times. Updated Table 1 maximum I/Os.
	01.0	—	Initial release.